Meera Chandrasekhar

List of Publications by Year
in descending order

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26	1,466	516561 16	580701 25
papers	citations	h-index	g-index

27	27	27	915
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Effects of uniaxial stress on the electroreflectance spectrum of Ge and GaAs. Physical Review B, 1977, 15, 2127-2144.	1.1	351
2	Effects of interband excitations on Raman phonons in heavily dopednâ^'Si. Physical Review B, 1978, 17, 1623-1633.	1.1	232
3	High-pressure studies of GaAs-Ga1â^'xAlxAs quantum wells of widths 26 to 150 AÌŠ. Physical Review B, 1986, 33, 8416-8423.	1.1	171
4	Pressure Raman effects and internal stress in network glasses. Physical Review B, 2005, 71, .	1.1	121
5	Study of the localized vibrations of boron in heavily doped Si. Physical Review B, 1980, 22, 4825-4833.	1.1	88
6	Pressure tuning of strains in semiconductor heterostructures: (ZnSe epilayer)/(GaAs epilayer). Physical Review B, 1991, 44, 11307-11314.	1.1	76
7	Photoluminescence studies of a GaAs-Ga1â^'xAlxAs superlattice at 8â€“300 K under hydrostatic pressure (0â€“70 kbar). Physical Review B, 1985, 31, 4106-4109.	1.1	62
8	Intraband Raman scattering by free carriers in heavily dopednâ^'Si. Physical Review B, 1977, 16, 3579-3595.	1.1	59
9	Luminescence and Raman spectra of CdS under hydrostatic pressure. Physical Review B, 1984, 30, 3316-3319.	1.1	44
10	Piezobirefringence above the fundamental edge in Si. Physical Review B, 1978, 18, 4301-4311.	1.1	39
11	Electronic transitions in CdTe under pressure. Physical Review B, 1990, 42, 3586-3590.	1.1	27
12	Low-temperature studies of the photoluminescence in CdS under hydrostatic pressure. Physical Review B, 1985, 31, 1219-1222.	1.1	25
13	Optical studies of strained pseudomorphic semiconductor heterostructures under external pressure. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1994, 70, 369-380.	0.6	23
14	Raman and modulated-reflectivity spectra of a strained pseudomorphic ZnTe epilayer on InAs under pressure. Physical Review B, 1994, 49, 2181-2184.	1.1	22
15	Electronic transitions in semiconductor quantum wells and epilayers under pressure. High Pressure Research, 1992, 9, 57-82.	0.4	17
16	Temperature dependence of strain in ZnSe(epilayer)/GaAs(epilayer). Journal of Applied Physics, 1995, 78, 6569-6573.	1.1	17
17	Pressure tuning of strain in CdTe/InSb epilayer: A photoluminescence and photomodulated reflectivity study. Journal of Applied Physics, 1993, 74, 4136-4144.	1.1	15
18	Impact of mobile technologyâ€based physics curriculum on preservice elementary teachers' technology selfâ€efficacy. Science Education, 2020, 104, 252-289.	1.8	14

#	Article	IF	Citations
19	Pressure-induced shifts of the fluorescence spectrum of rhodamine 6G in solution. Applied Optics, 1985, 24, 2779.	2.1	12
20	Electronic transitions in bulkAl0.3Ga0.7As under hydrostatic pressure. Physical Review B, 1991, 44, 13404-13417.	1.1	11
21	A new method to measure stress-induced birefringence in an opaque material: Stress-induced Raman scattering. Journal of the Optical Society of America, 1978, 68, 523.	1.2	10
22	Spectroscopic studies of strained-layer GaSbî—¸AlSb superlattices. Surface Science, 1990, 228, 322-325.	0.8	9
23	Quantum wells and deep impurity levels under hydrostatic pressure. Superlattices and Microstructures, 1988, 4, 107-114.	1.4	8
24	Effects of hydrostatic pressure on the low-temperature photoluminescence spectrum of heavily doped CdS. Physical Review B, 1985, 31, 6574-6578.	1.1	6
25	Photoreflectance studies of electronic transitions in quantum well structures under high presure. , 1990, , .		4
26	Deep center inAl0.3Ga0.7As. Physical Review B, 1991, 43, 12126-12129.	1.1	3